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HR EXCELLENCE IN RESEARCH



Fundamentals of Photovoltaic Conversion and Solar Cell Performance

Katarzyna Gwóźdź

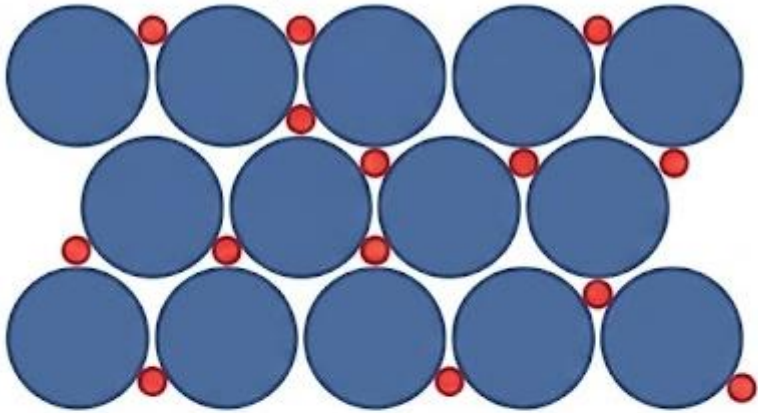
Department of Experimental Physics
Faculty of Fundamental Problems of Technology
Wrocław University of Science and Technology
Wrocław, Poland

Outline

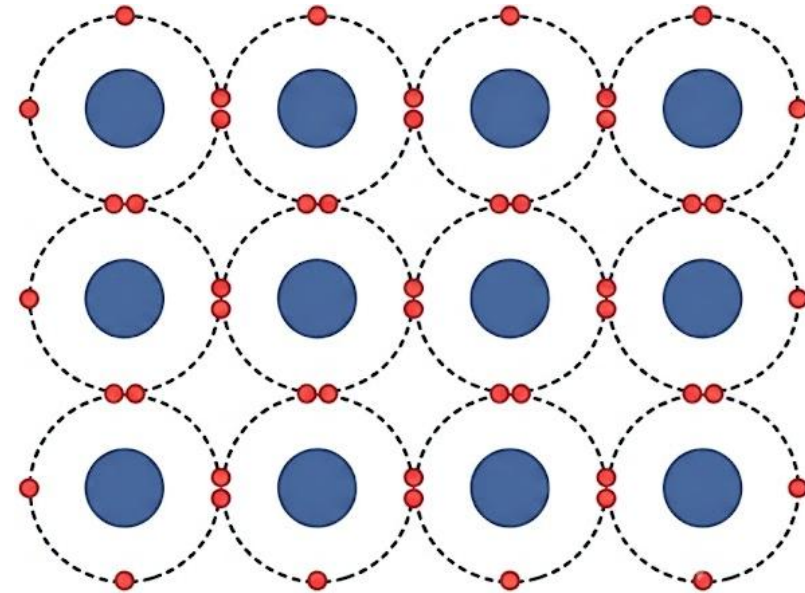
1. Structure and operating principles of the basic semiconductor p-n junction.
2. Mechanisms of charge carrier generation and extraction under sunlight.
3. Key electrical parameters used to evaluate solar cell performance.
4. Primary optical and electrical loss mechanisms that limit overall efficiency.



Semiconductors

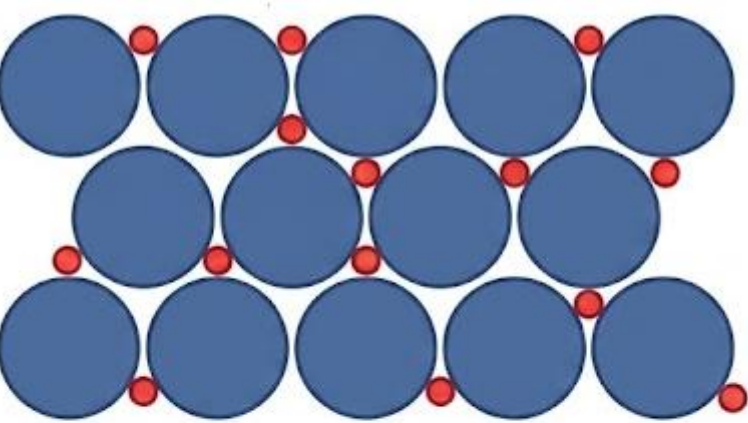


Conductor

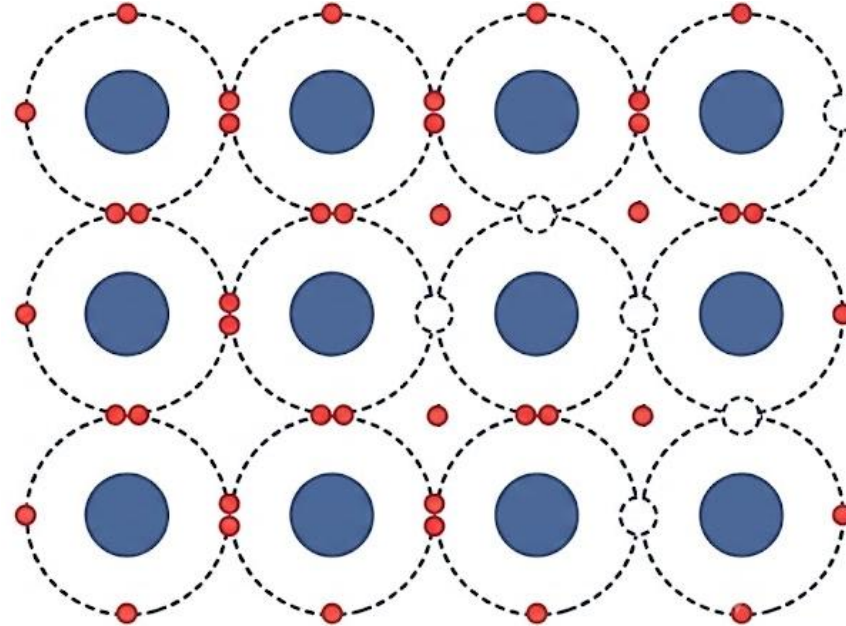


Insulator

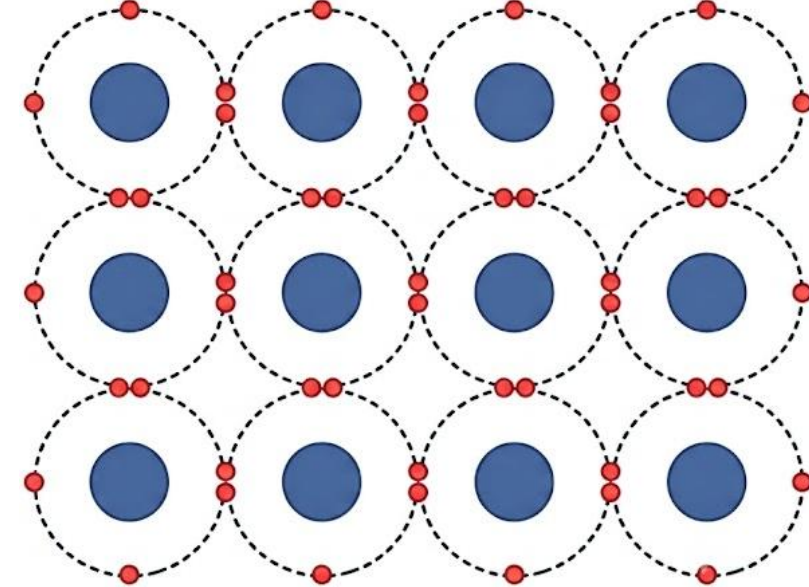
Semiconductors



Conductor



Semiconductor



Insulator

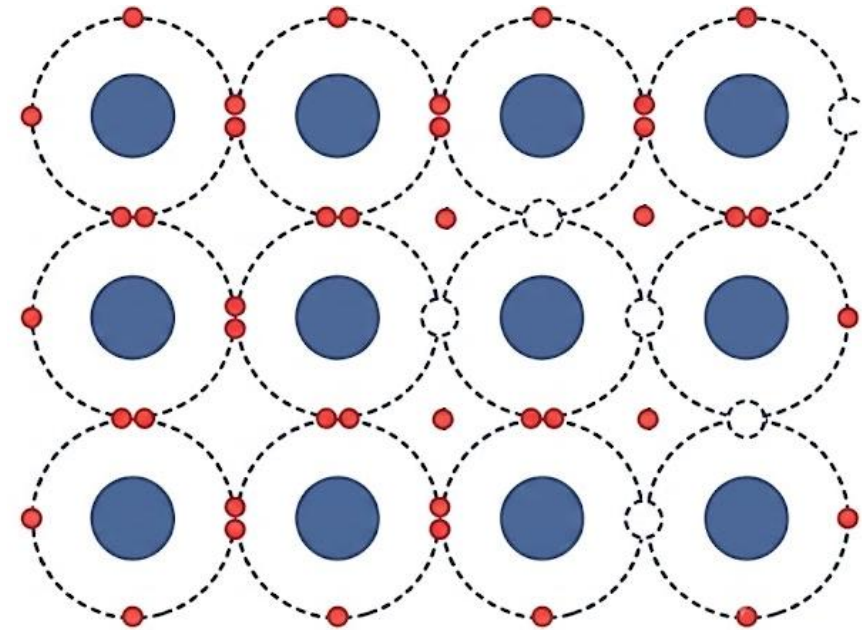
Semiconductors

More free electrons:

Temperature

Light

Doping



Semiconductor

Semiconductors

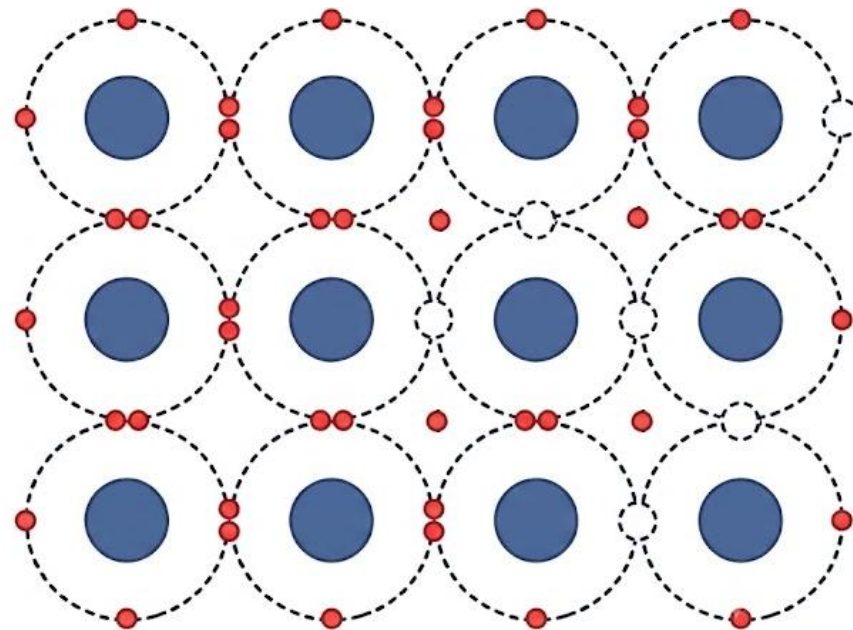
More free electrons:

Temperature

Light

Doping

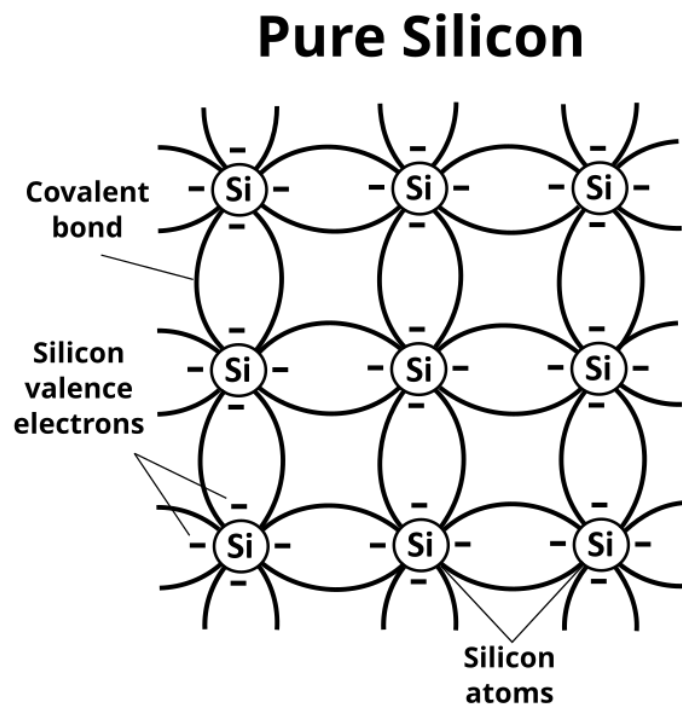
Energy of the photon must be higher than the energy gap of the semiconductor.



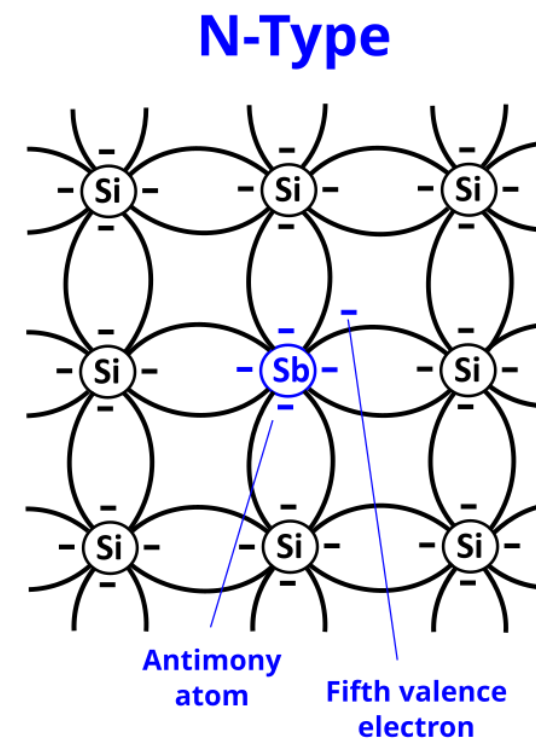
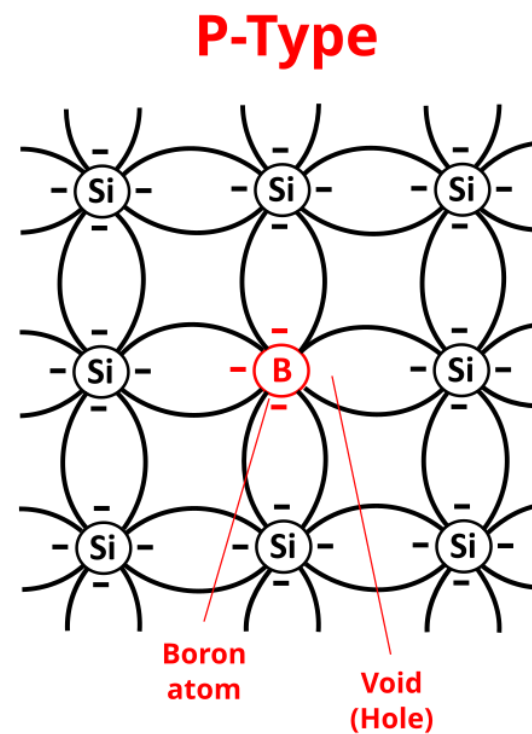
Semiconductor

Doping

Intrinsic (Undoped)



Extrinsic (Doped)





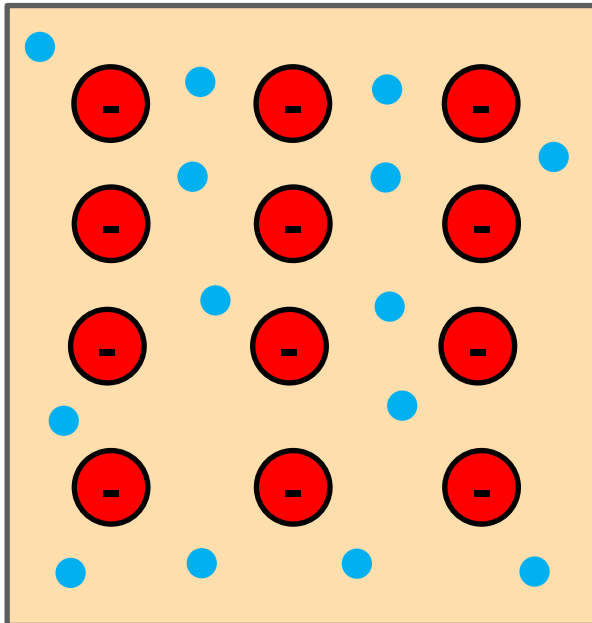
Negatively charged ion



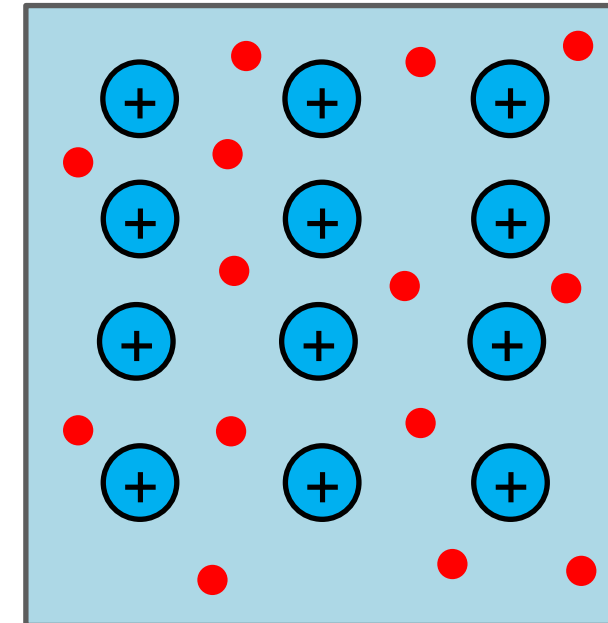
Positively charged ion

P-n junction

p-type



n-type



● Electron

● Hole

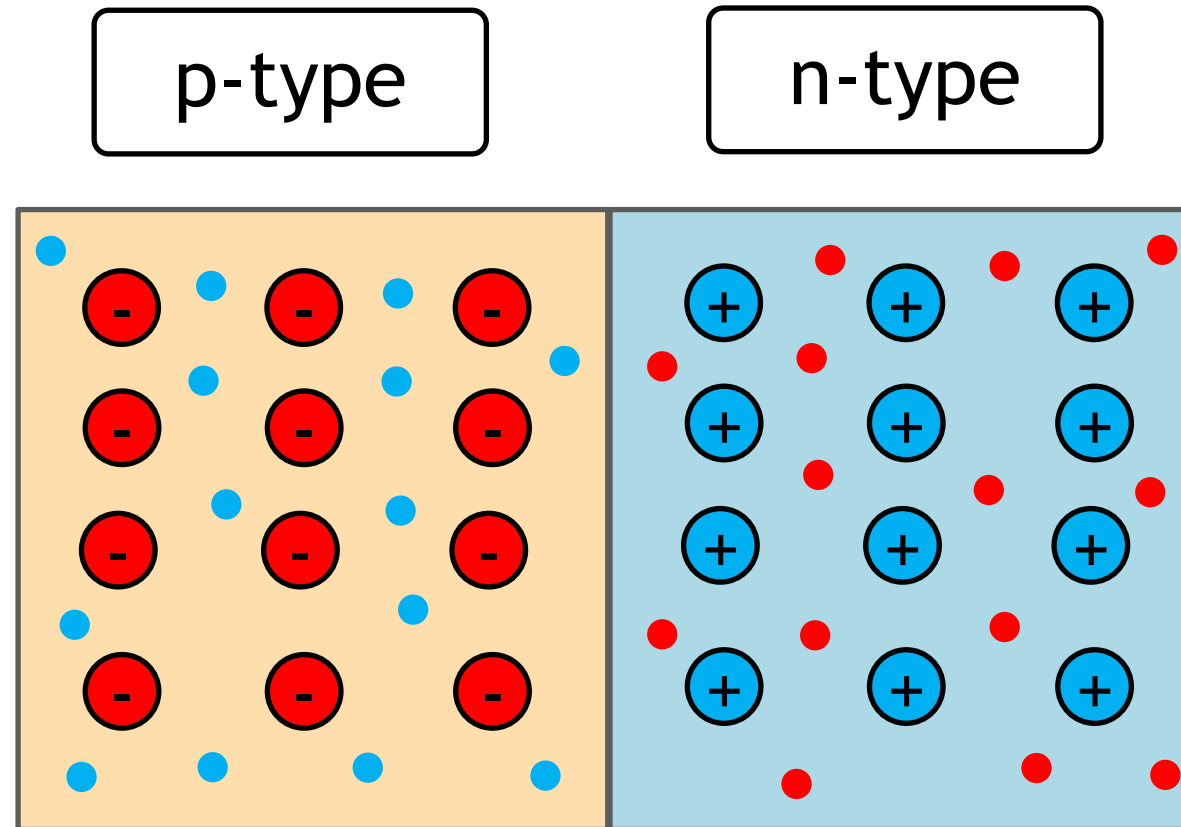


Negativly charged ion



Positivly charged ion

P-n junction



● Electron

● Hole

P-n junction



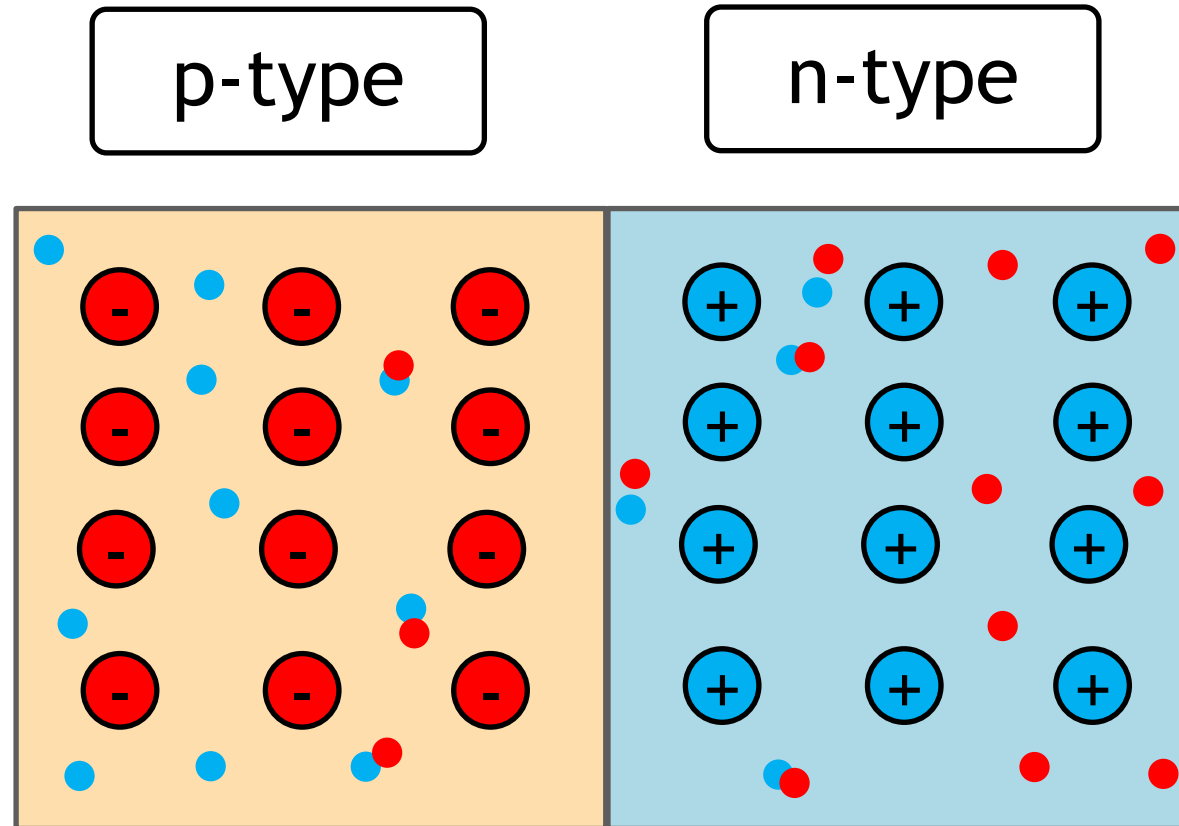
Negatively charged ion



Positively charged ion

● Electron

● Hole



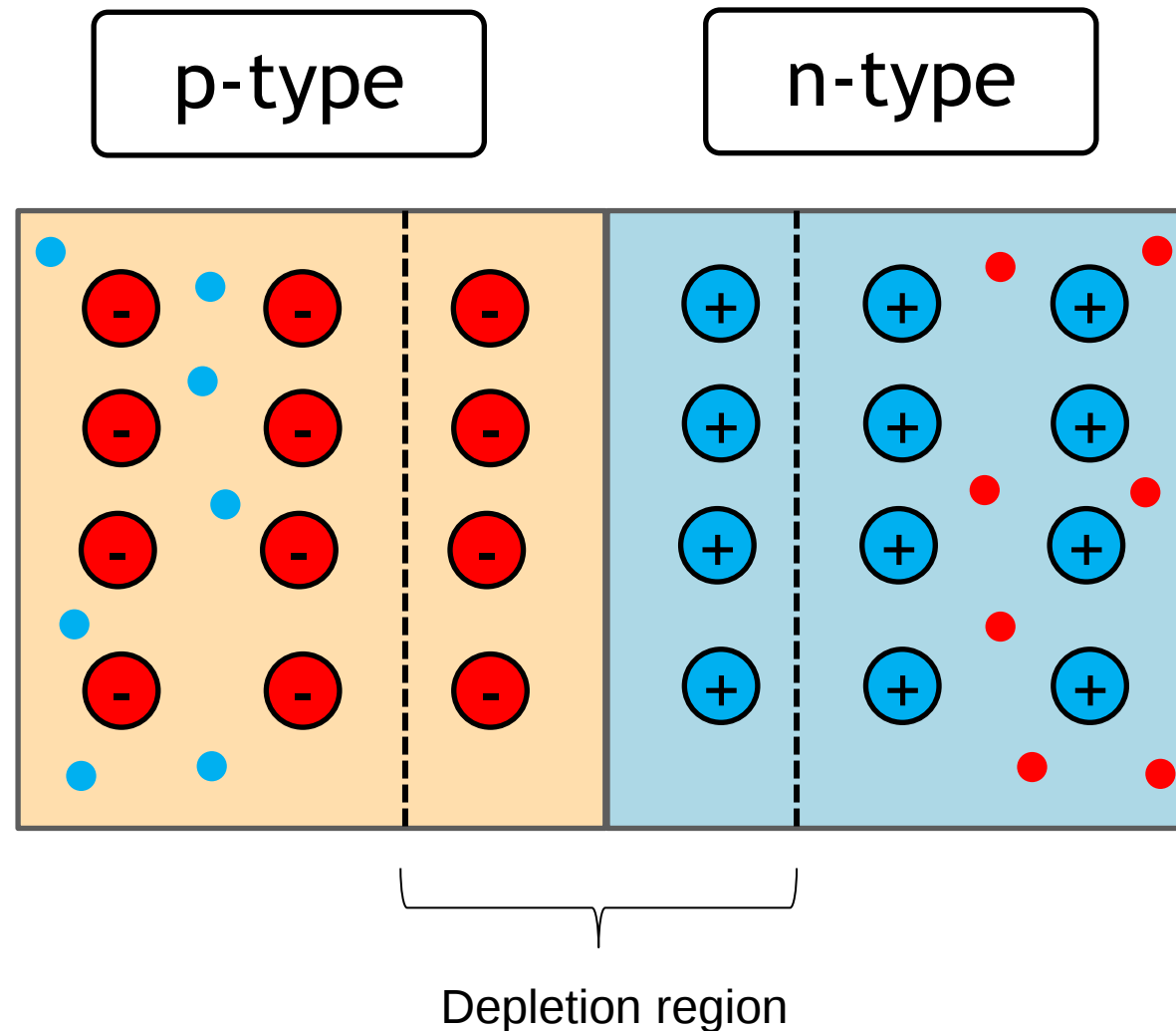


Negatively charged ion



Positively charged ion

P-n junction



● Electron

● Hole



Negatively charged ion

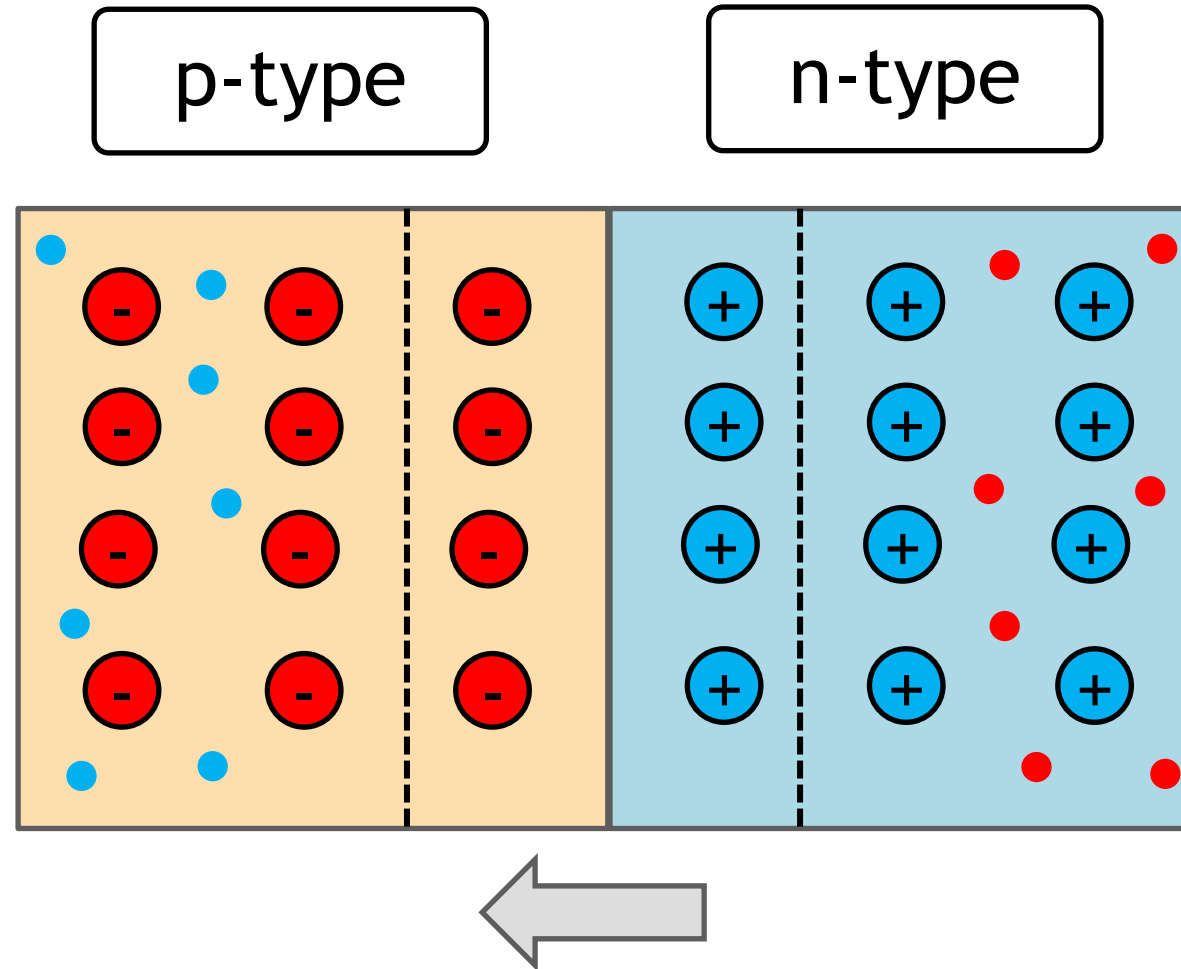


Positively charged ion

P-n junction

● Electron

● Hole



Built-in electric field



Negatively charged ion



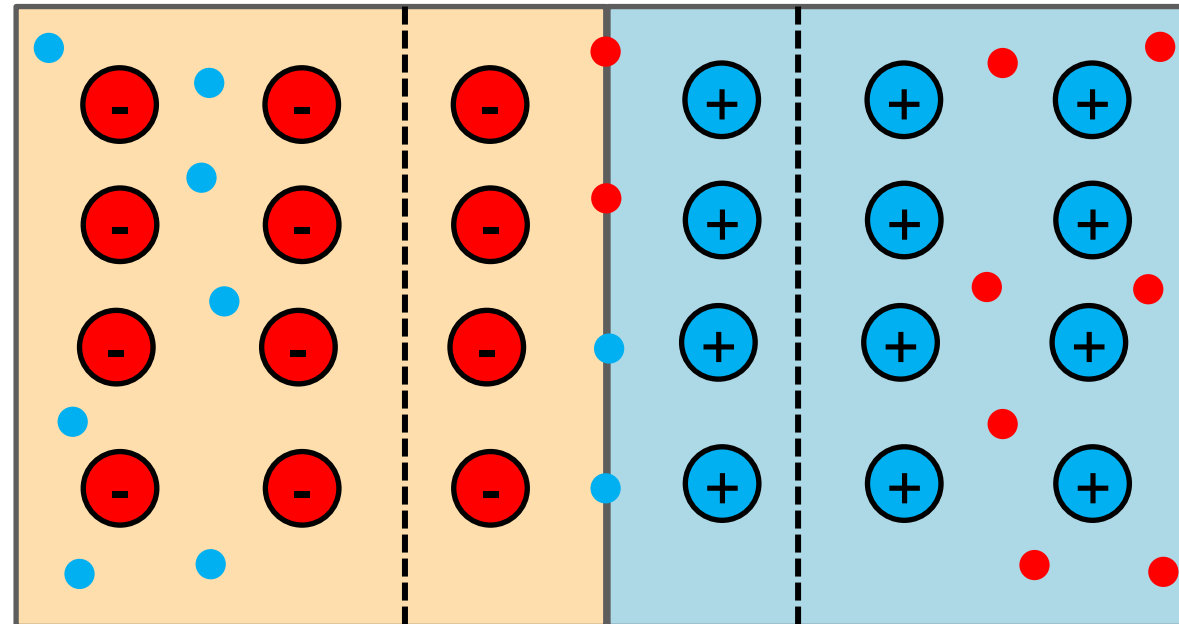
Positively charged ion

P-n junction - light



● Electron

● Hole



Built-in electric field



Negatively charged ion



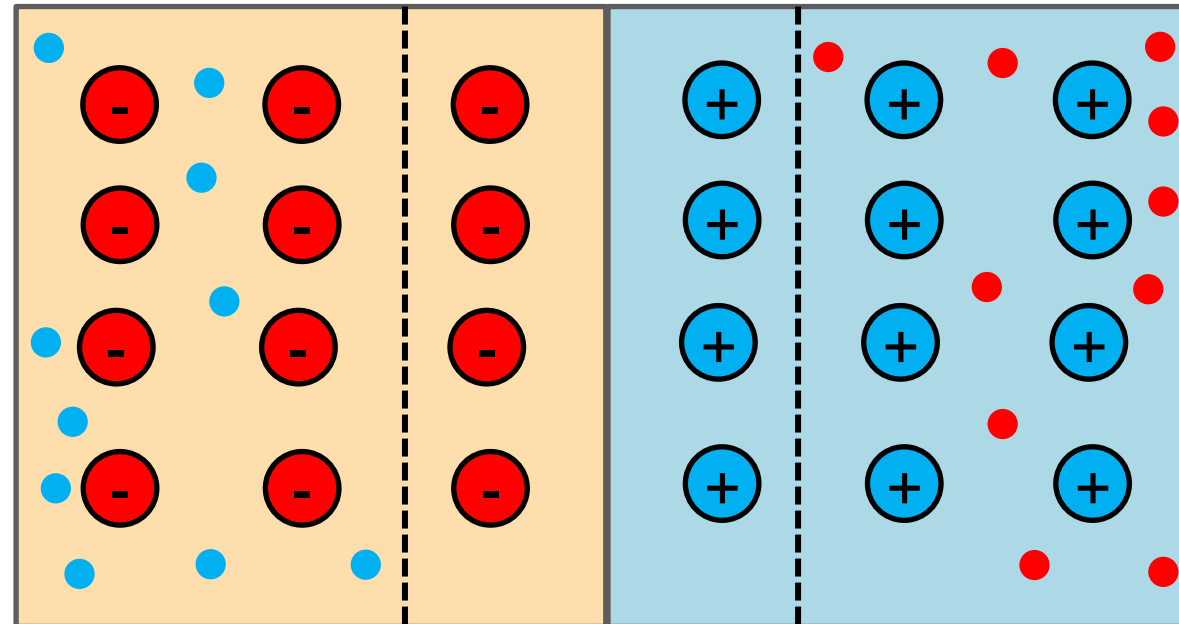
Positively charged ion

P-n junction - light



● Electron

● Hole



Built-in electric field

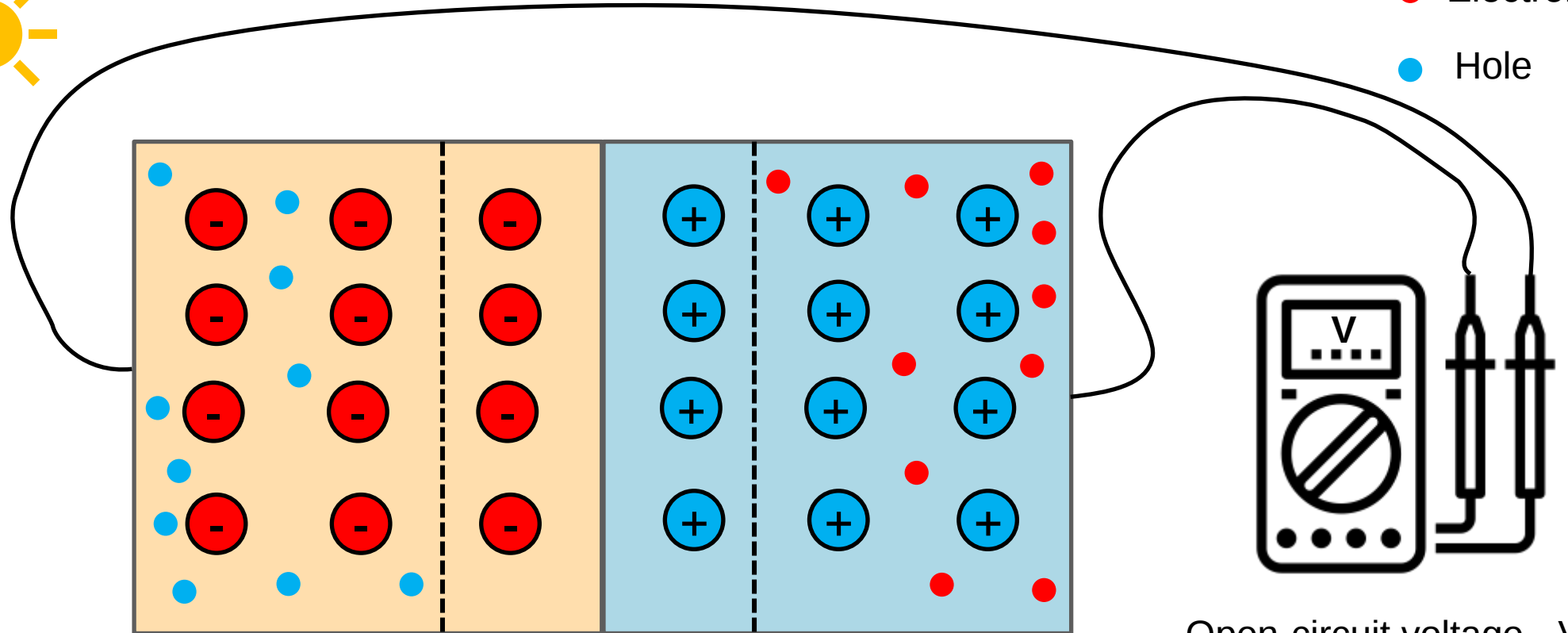


Negatively charged ion



Positively charged ion

P-n junction - light



● Electron

● Hole

Open-circuit voltage - V_{oc}

Built-in electric field



Negatively charged ion

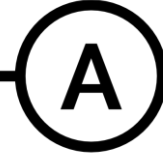


Positively charged ion

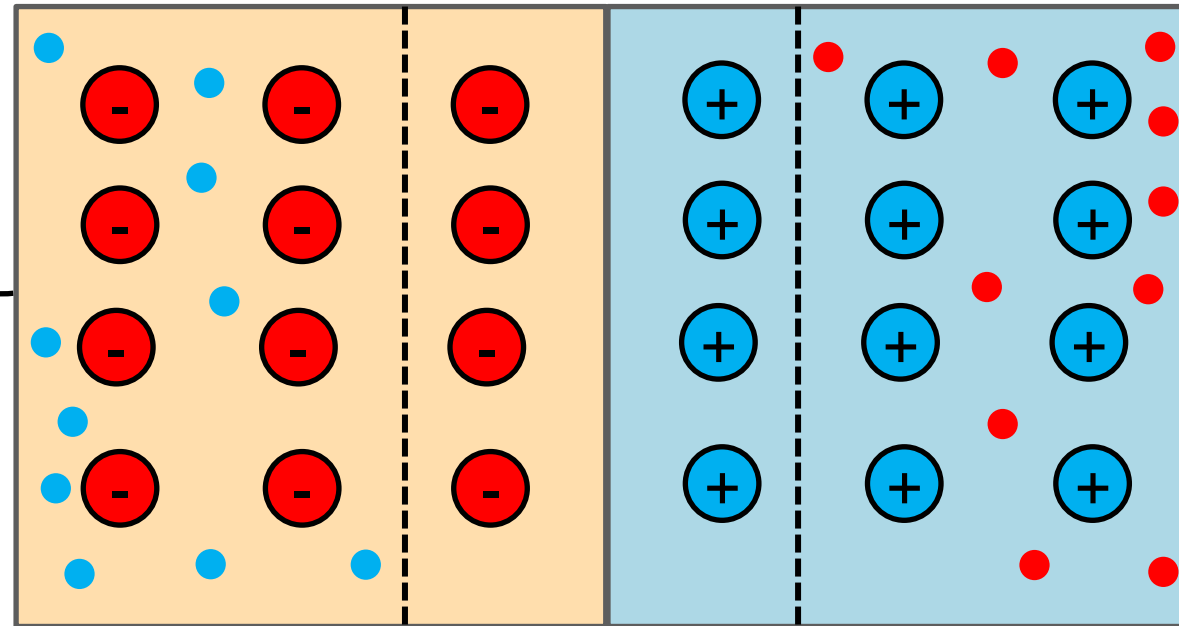
P-n junction - light

● Electron

● Hole

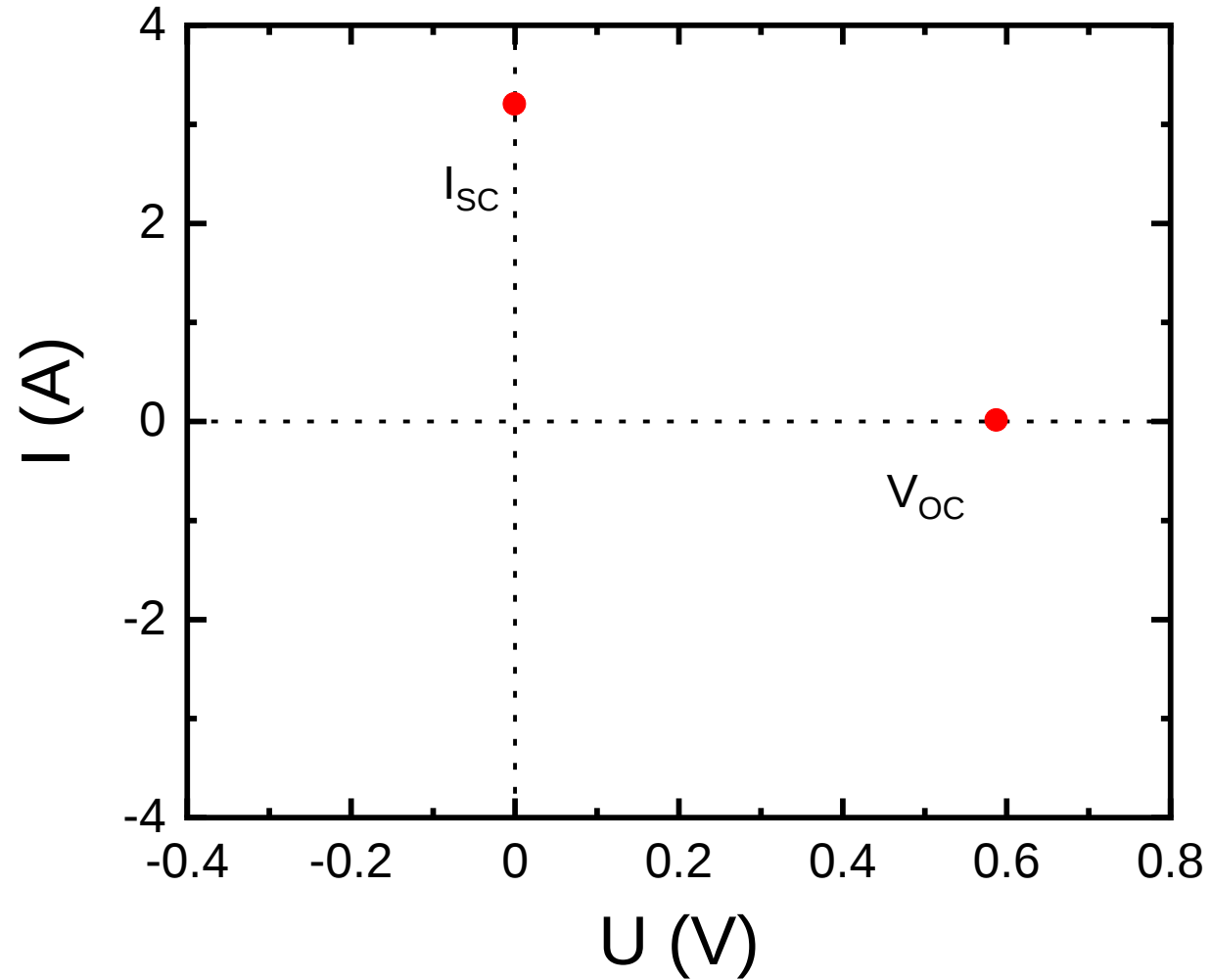


Short-circuit current - I_{sc}

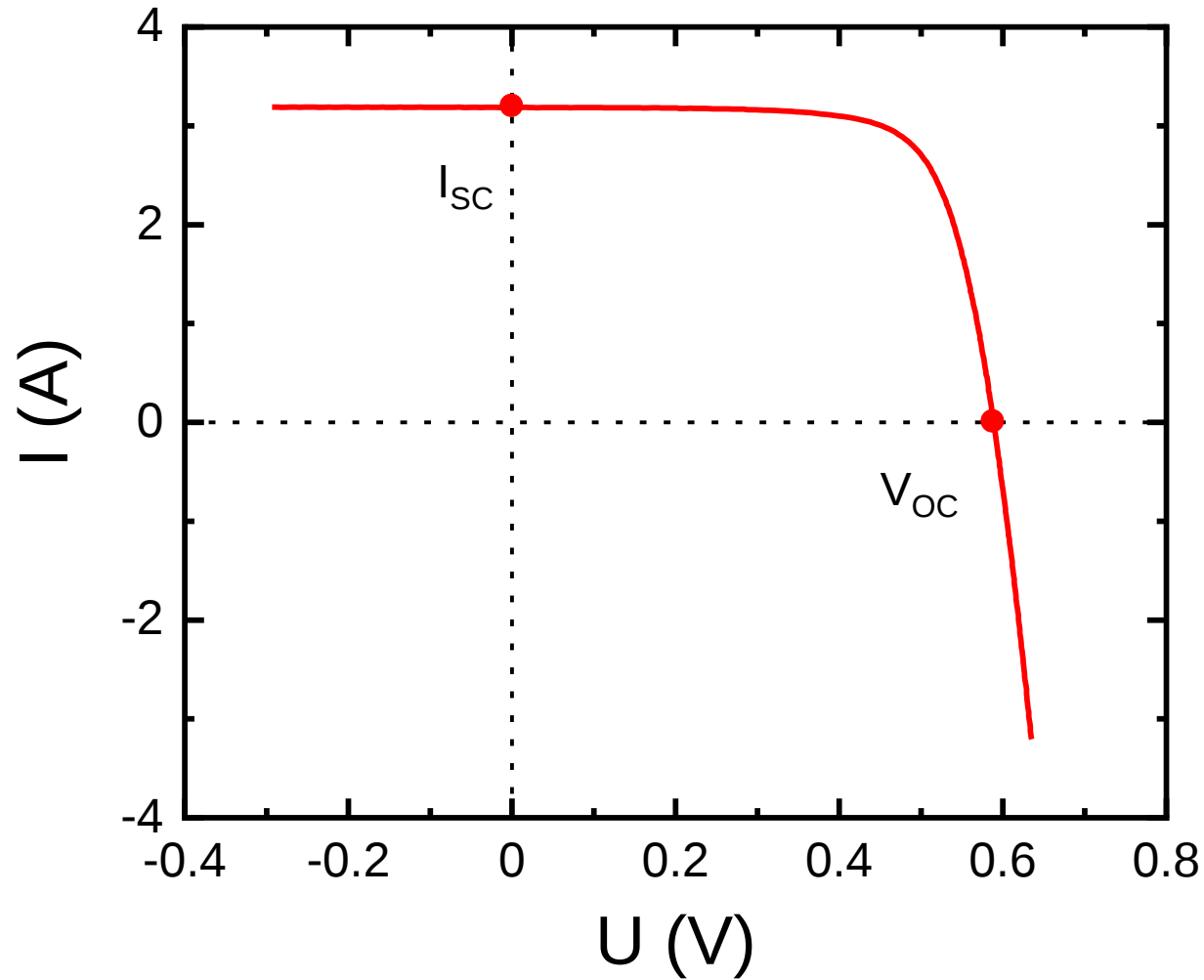


Built-in electric field

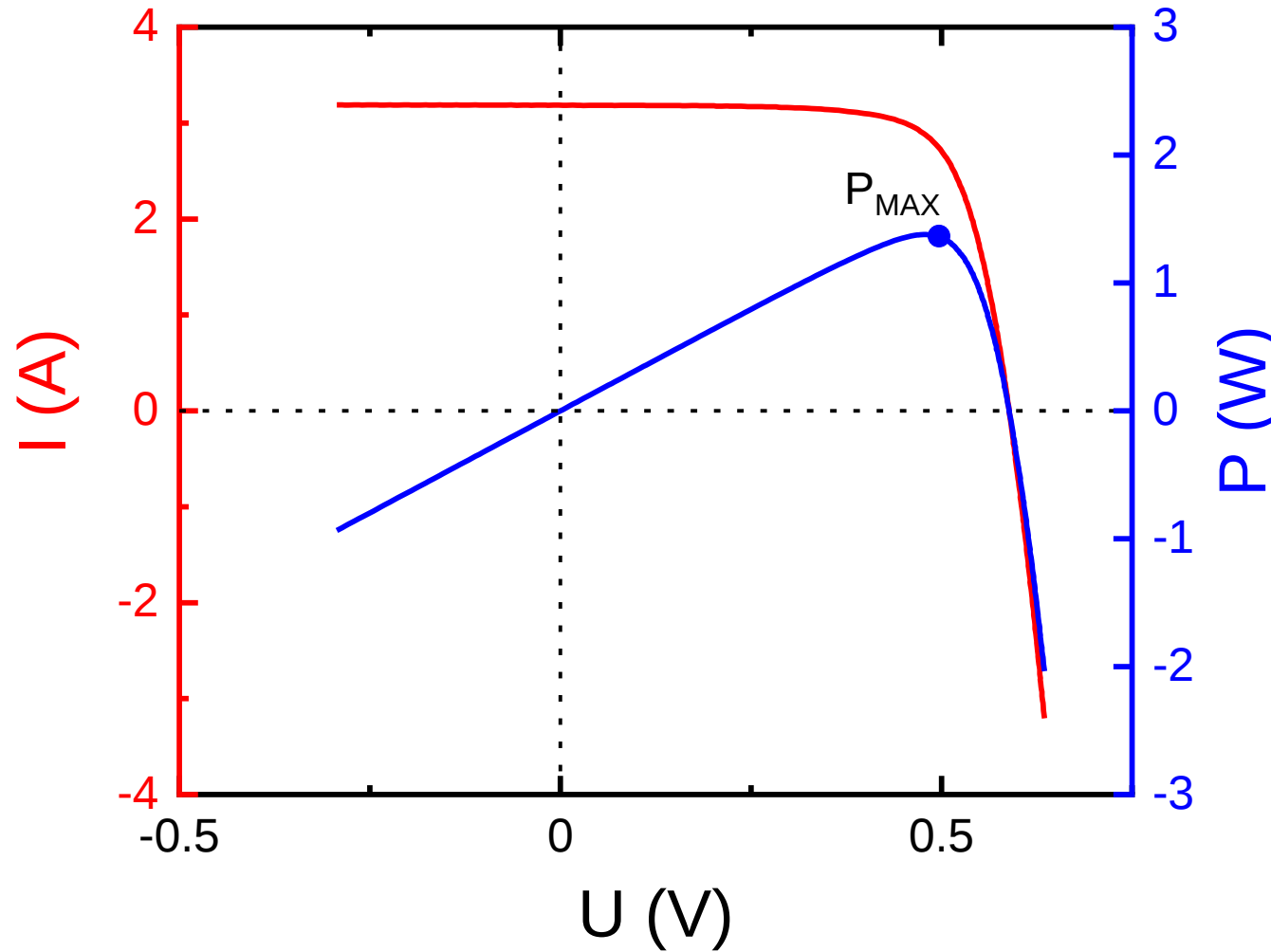
I-V curve



I-V curve



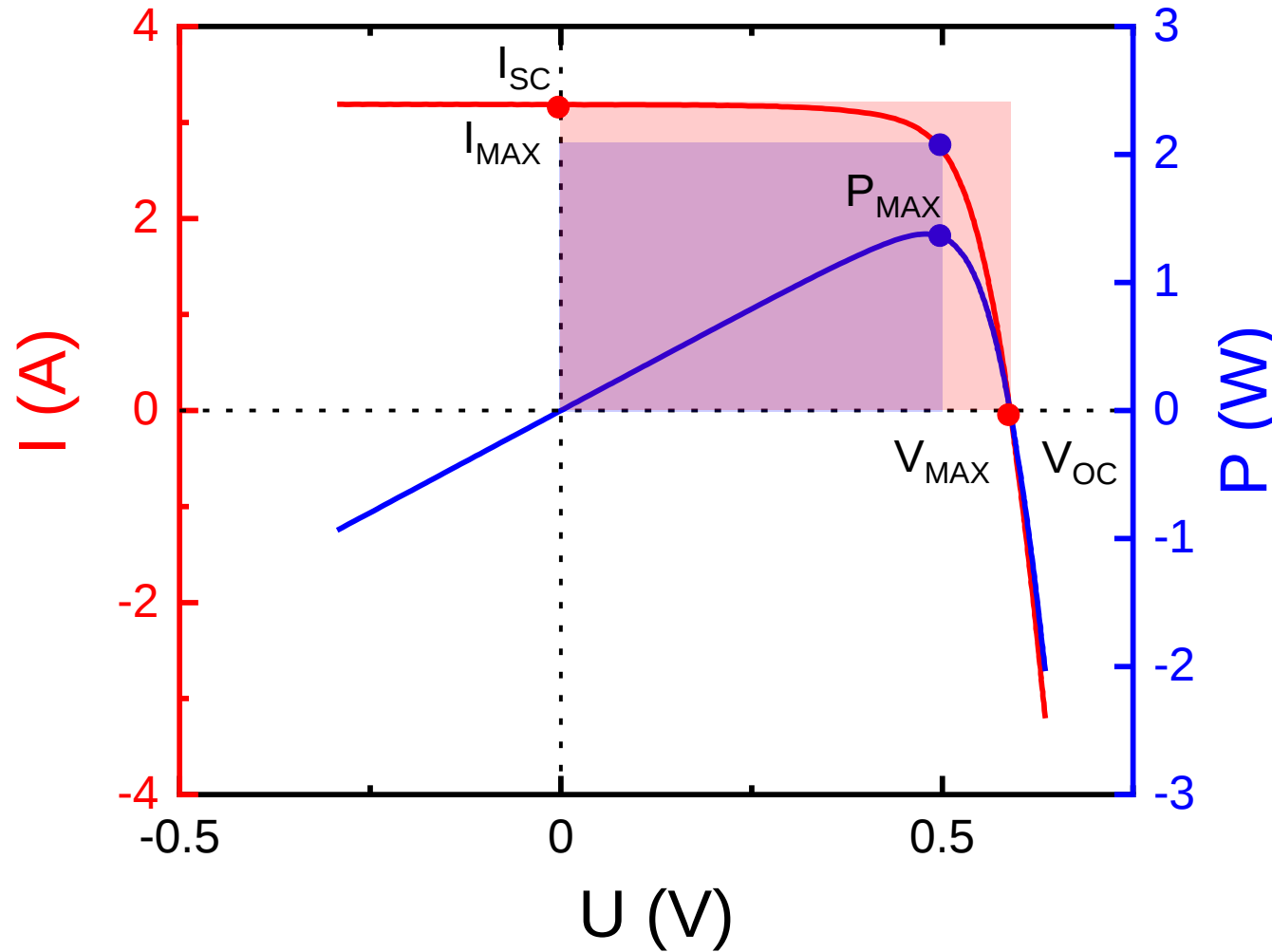
I-V curve



$$P = U \times I$$

$$P_{MAX} = U_{MAX} \times I_{MAX}$$

I-V curve

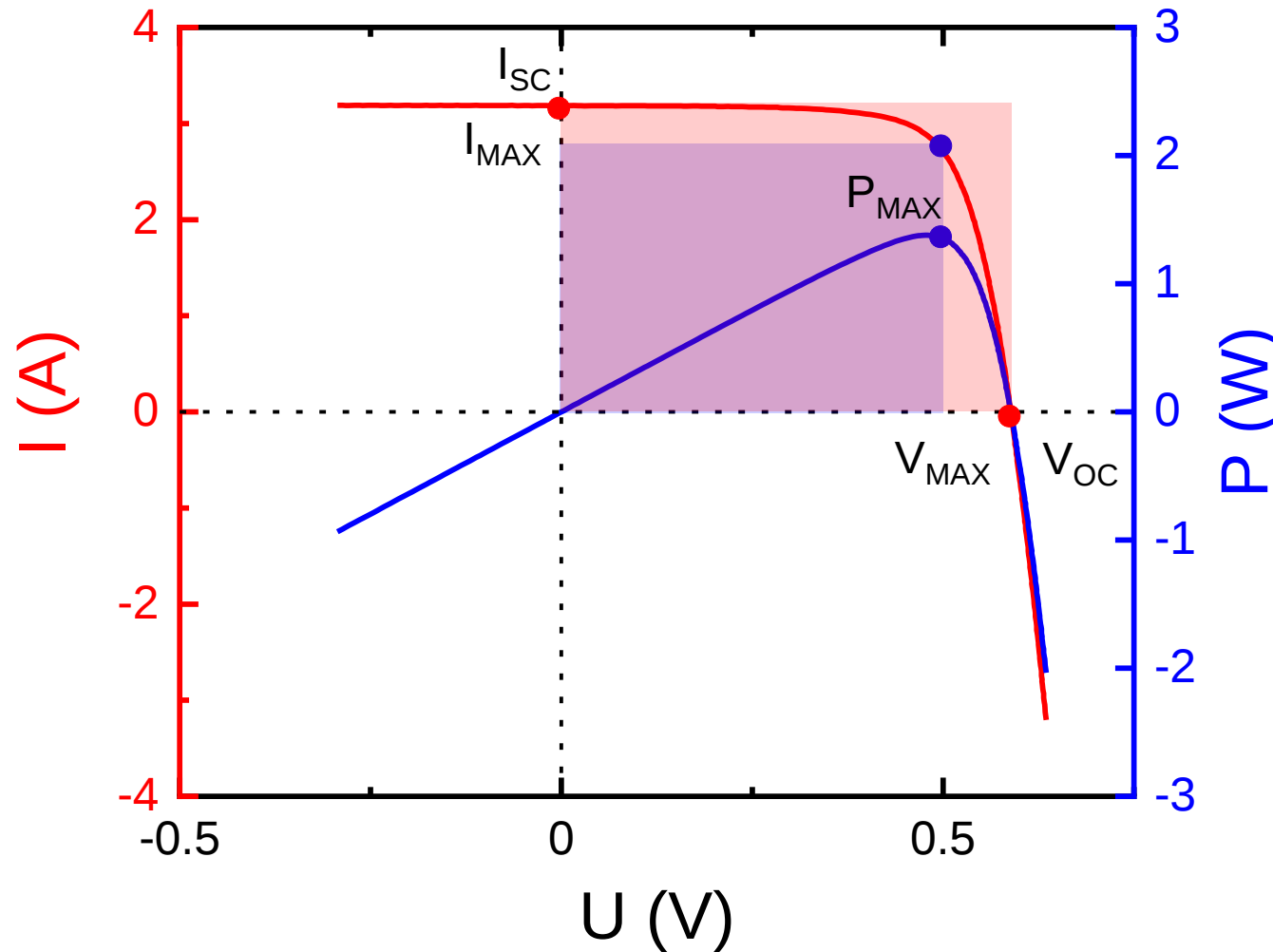


$$P = U \times I$$

$$P_{MAX} = V_{MAX} \times I_{MAX}$$

$$Fill\ Factor = \frac{I_{MAX} \times V_{MAX}}{I_{SC} \times V_{OC}}$$

Efficiency



$$P = U \times I$$

$$P_{MAX} = V_{MAX} \times I_{MAX}$$

$$FF = \frac{I_{MAX} \times V_{MAX}}{I_{SC} \times V_{OC}}$$

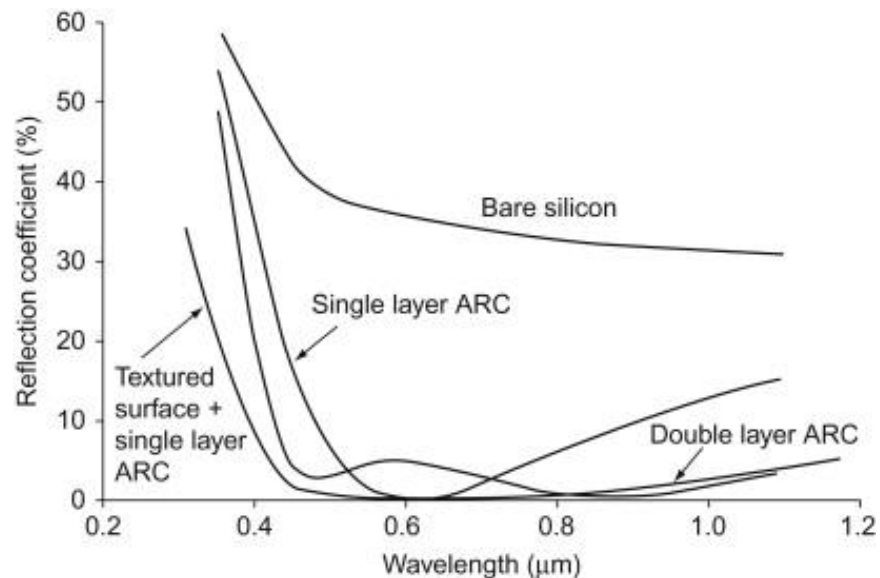
$$\eta = \frac{FF \times I_{SC} \times V_{OC}}{P_{in}}$$

Efficiency - losses

Optical

Electrical

Efficiency - losses



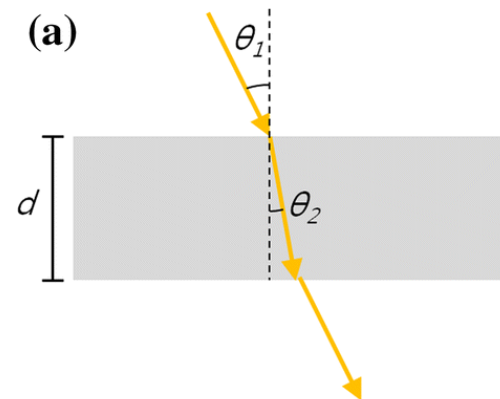
<https://www.pveducation.org/pvcdrom/design-of-silicon-cells/anti-reflection-coating-color>

Optical

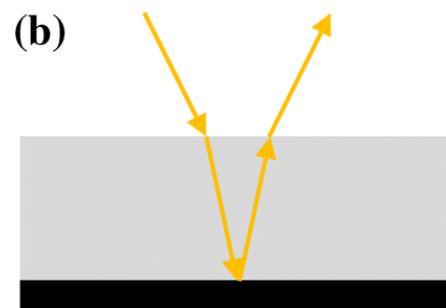
Reflection

Electrical

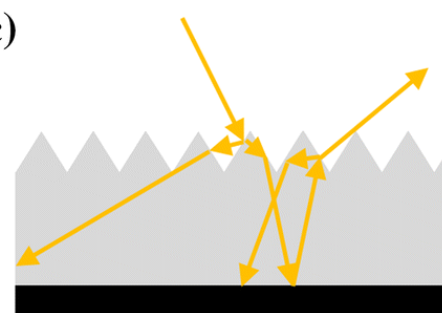
(a)



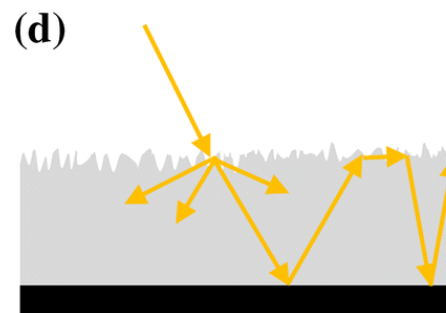
(b)



(c)



(d)



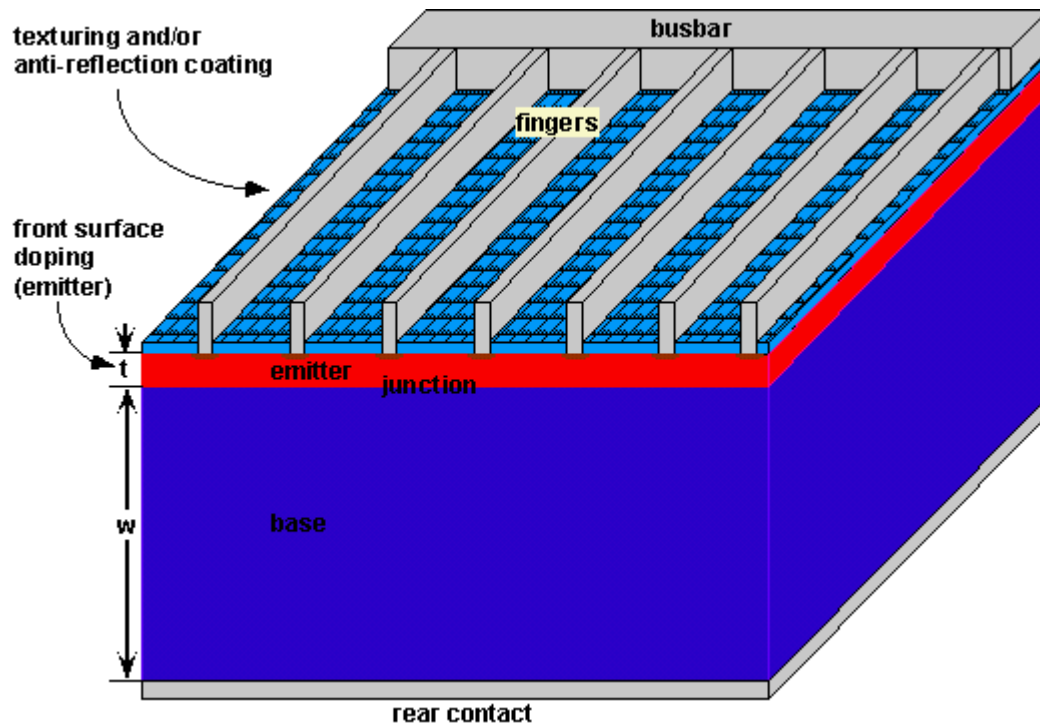
Efficiency - losses

Optical

Reflection

Shadowing

Electrical



Efficiency - losses

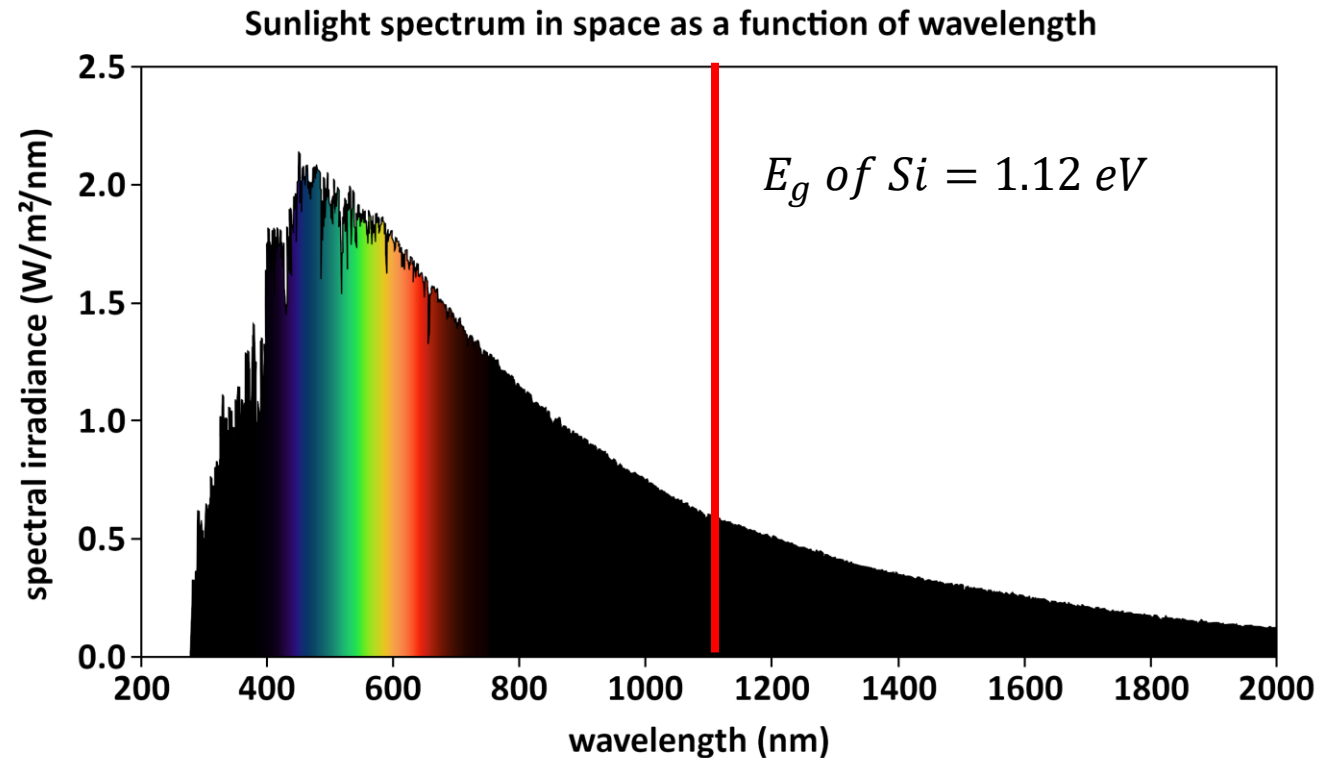
Optical

Reflection

Shadowing

Incomplete absorption

Electrical



Efficiency - losses



Optical

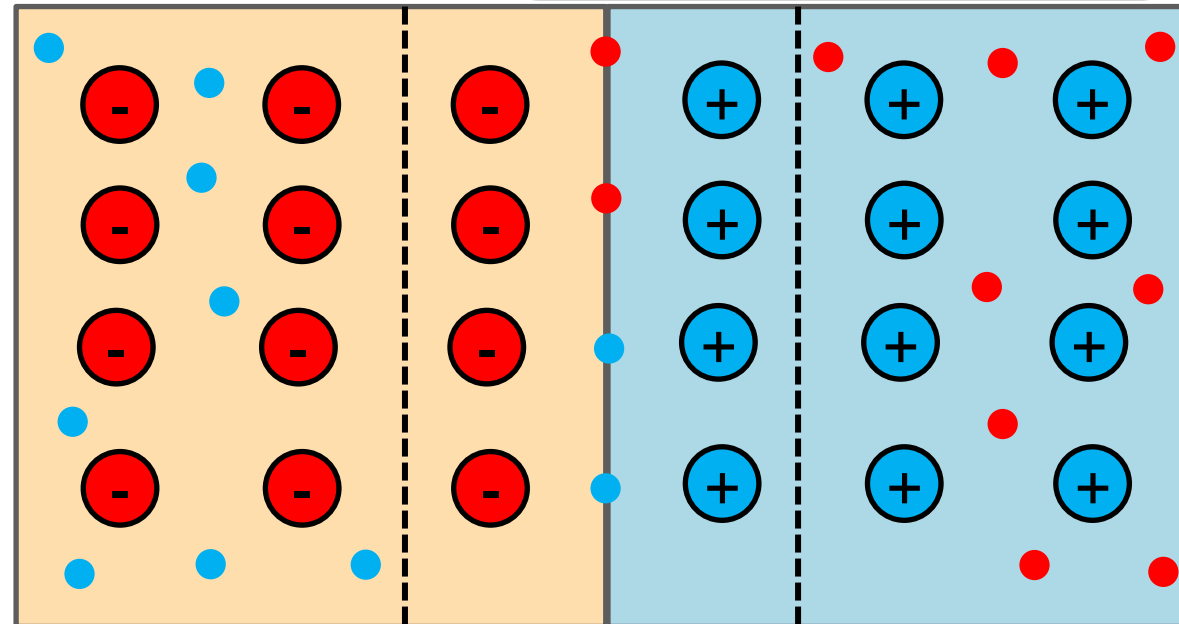
Reflection

Shadowing

Incomplete absorption

Electrical

Recombination



Built-in electric field

Efficiency - losses



Optical

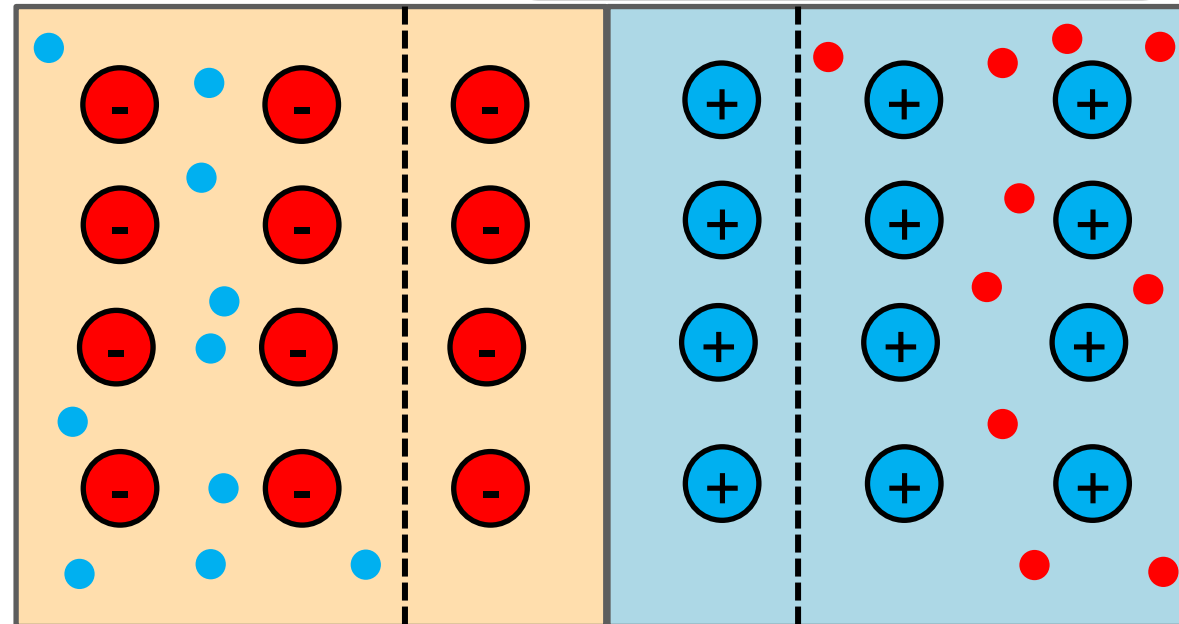
Reflection

Shadowing

Incomplete absorption

Electrical

Recombination



Built-in electric field

Efficiency - losses



Optical

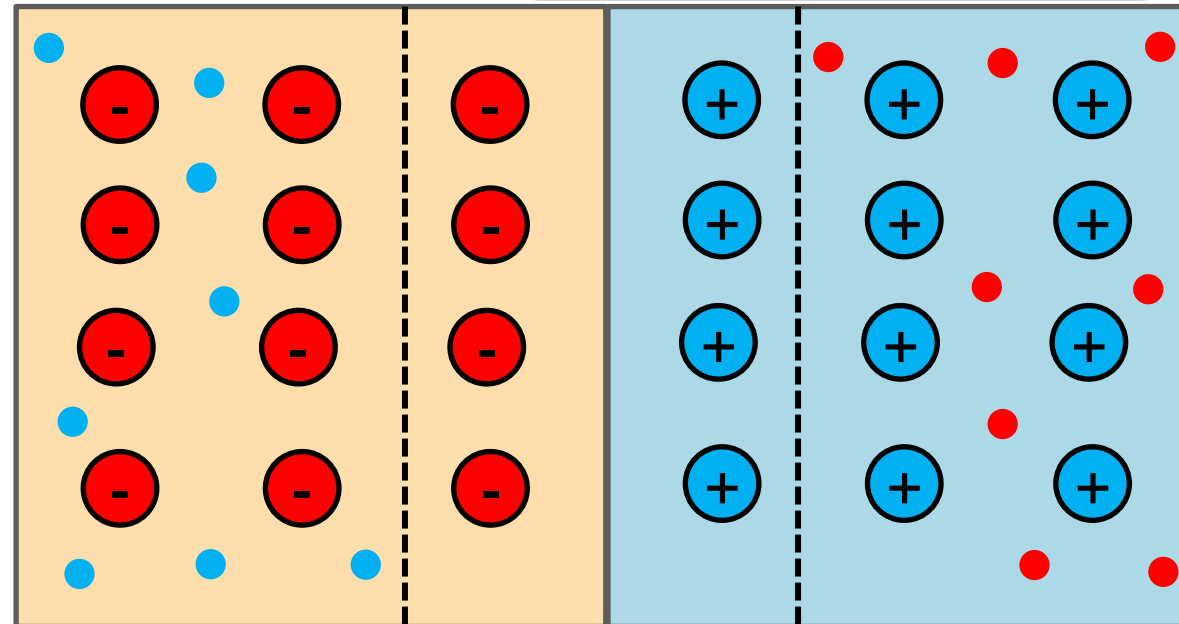
Reflection

Shadowing

Incomplete absorption

Electrical

Recombination



Built-in electric field

Efficiency - losses

Optical

Reflection

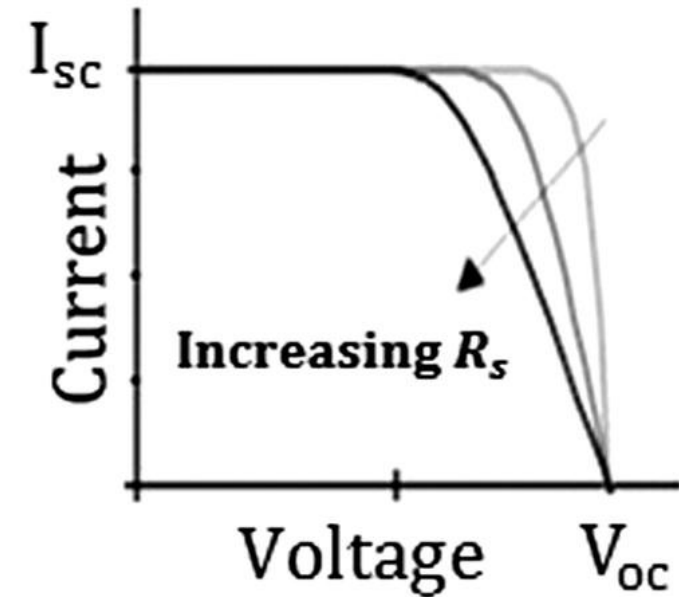
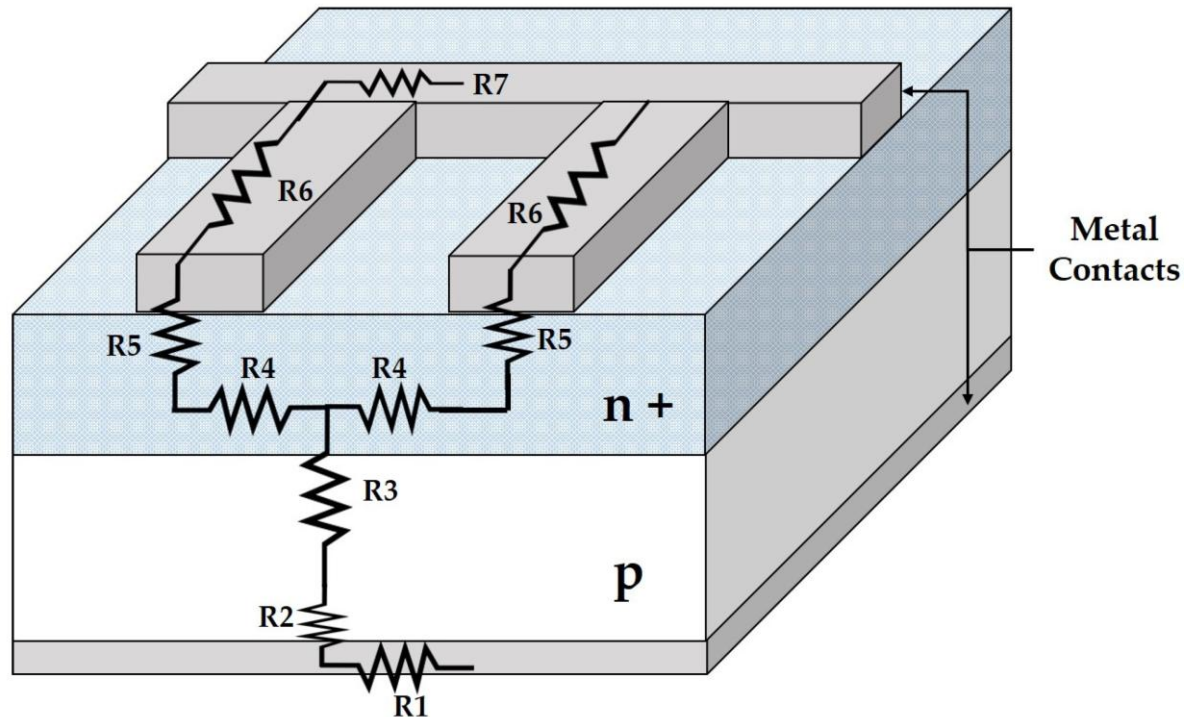
Shadowing

Incomplete absorption

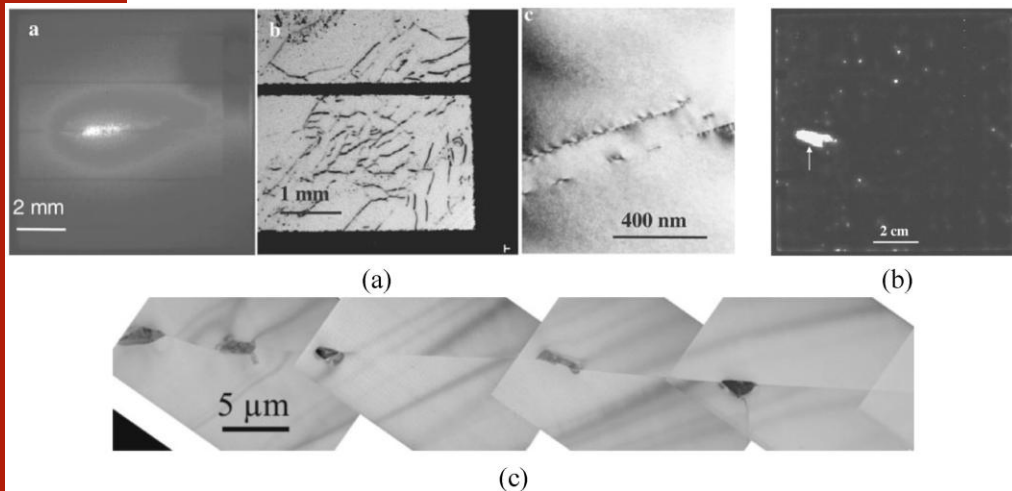
Electrical

Recombination

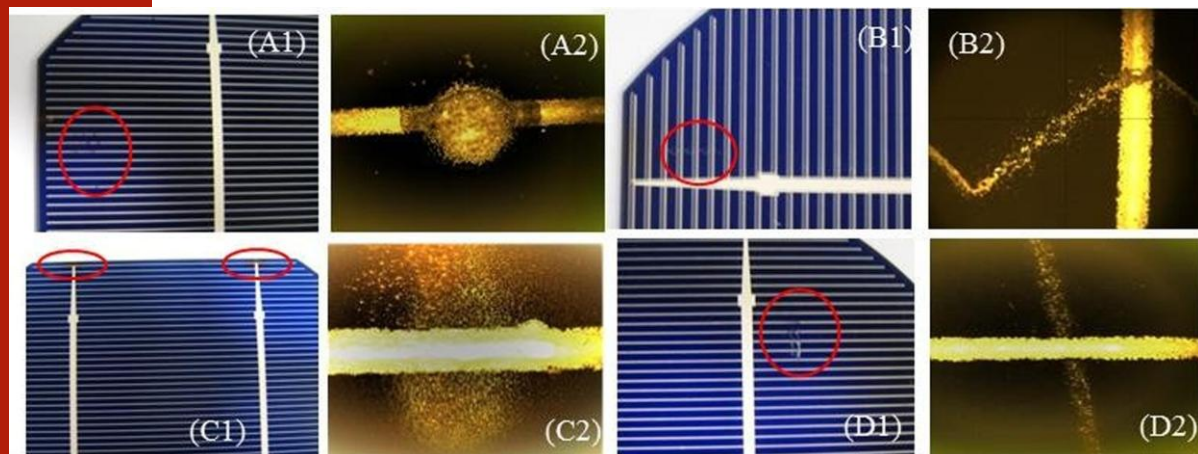
Series resistance



Efficiency - losses



Ravi Kumar, Rajesh Gupta, Shunts in crystalline silicon PV modules: A comprehensive review of investigation, characterization, and mitigation, Solar Energy Materials and Solar Cells, Volume 277, 2024, 113121, <https://doi.org/10.1016/j.solmat.2024.113121>.



María Cruz López-Escalante, Francisco Martín Jiménez, Mercedes Gabás Pérez, Dietmar Leinen, José Ramón Ramos Barrado, Shunt resistance criterion: Design and implementation for industrial silicon solar cell production, Solar Energy, Volume 206, 2020, Pages 269-278, <https://doi.org/10.1016/j.solener.2020.05.092>.

Optical

Reflection

Shadowing

Incomplete absorption

Electrical

Recombination

Series resistance

Shunt resistance

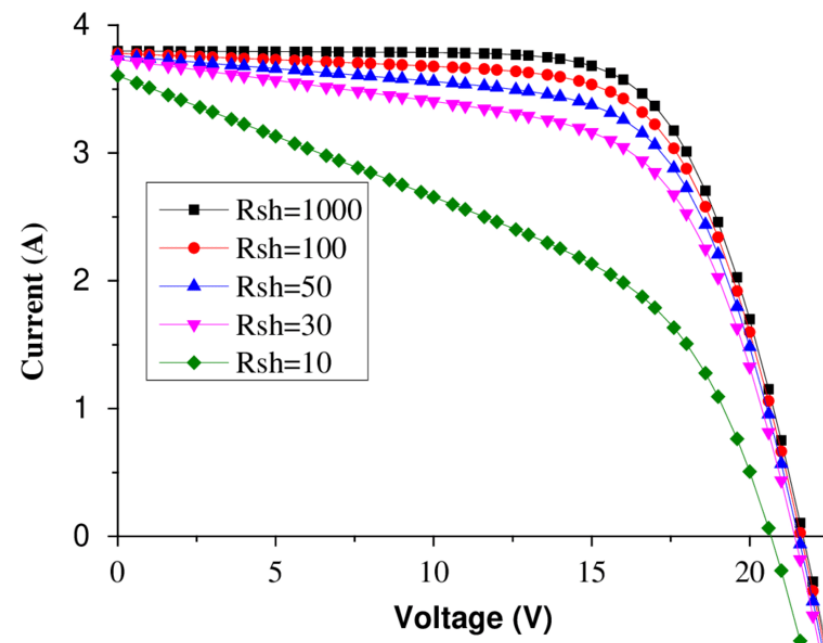


Fig. 9. Influence of quality of the shunt resistance on I (V)



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Thank you for your attention!

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